

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A semiconductor device, comprising:

a capacitor having a bottom electrode, a dielectric layer formed on the bottom electrode, and an upper electrode formed on the dielectric layer, the capacitor being formed on a semiconductor substrate, wherein the bottom electrode, the dielectric layer, and the upper electrode are vertically arranged;

a first insulating layer formed on the semiconductor substrate to cover the capacitor;

a plurality of first contact plugs formed in a plurality of first via holes of the first insulating layer, each of the plurality of first contact plugs being electrically connected to either the bottom electrode or the upper electrode;

a first metal wiring formed on the first insulating layer and connected to the bottom electrode through one of the first contact plugs;

a second insulating layer formed on the first insulating layer;

a second contact plug in the second insulating layer formed on the first insulating layer and connected to the upper electrode through another one of the first contact plugs;

an anti-fuse formed in certain thickness on the second contact plug in a second via hole of the second insulating layer and electrically connected to the second contact plug;

a third contact plug filling the second via hole and formed within the anti-fuse, wherein the third contact plug does not directly contact the second insulating layer; and

a second metal wiring formed on the second insulating layer and electrically connected to the third contact plug and the anti-fuse.

2. (Original) The semiconductor device of claim 1, wherein the first and second metal wirings are arranged perpendicular to each other.

3. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

forming a capacitor having a bottom electrode, a dielectric layer formed on the bottom electrode and an upper electrode formed on the dielectric layer on a semiconductor substrate;

wherein the bottom electrode, the dielectric layer, and the upper electrode are vertically arranged;

- forming a first insulating layer on the semiconductor substrate to cover the capacitor;
- forming a plurality of first via holes exposing surfaces of the bottom electrode and the upper electrode by selectively patterning the first insulating layer;
- forming a plurality of first contact plugs by filling the first via holes with metal materials;
- forming first metal wiring connected to the bottom electrode through one of the plurality of first contact plugs and forming a second contact plug connected to the upper electrode through another one of the plurality of first contact plugs, on the first insulating layer;
- forming a second insulating layer on the first insulating layer;
- forming a second via hole exposing a surface of the second contact plug by selectively patterning the second insulating layer;
- successively depositing first and second metal layers on the second insulating layer including the second via hole;
- forming an anti-fuse on the second contact plug in the second via hole and a third contact plug within the anti-fuse by planarizing the first and second metal layers with the second insulating layer; and
- forming second metal wiring electrically connected to the anti-fuse and the third contact plug, on the second insulating layer.